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Cost-effective, ester-based molecular doping in silicon.

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1. Supplementary Information

1.1. Non-linear fitting curves

Figure S1 shows the nonlinear fit results, alongside the point-wise fitting errors. Table 1 lists the resulting fitting parameters and the corresponding χ^2 accumulated error values, indication an excellent fit.

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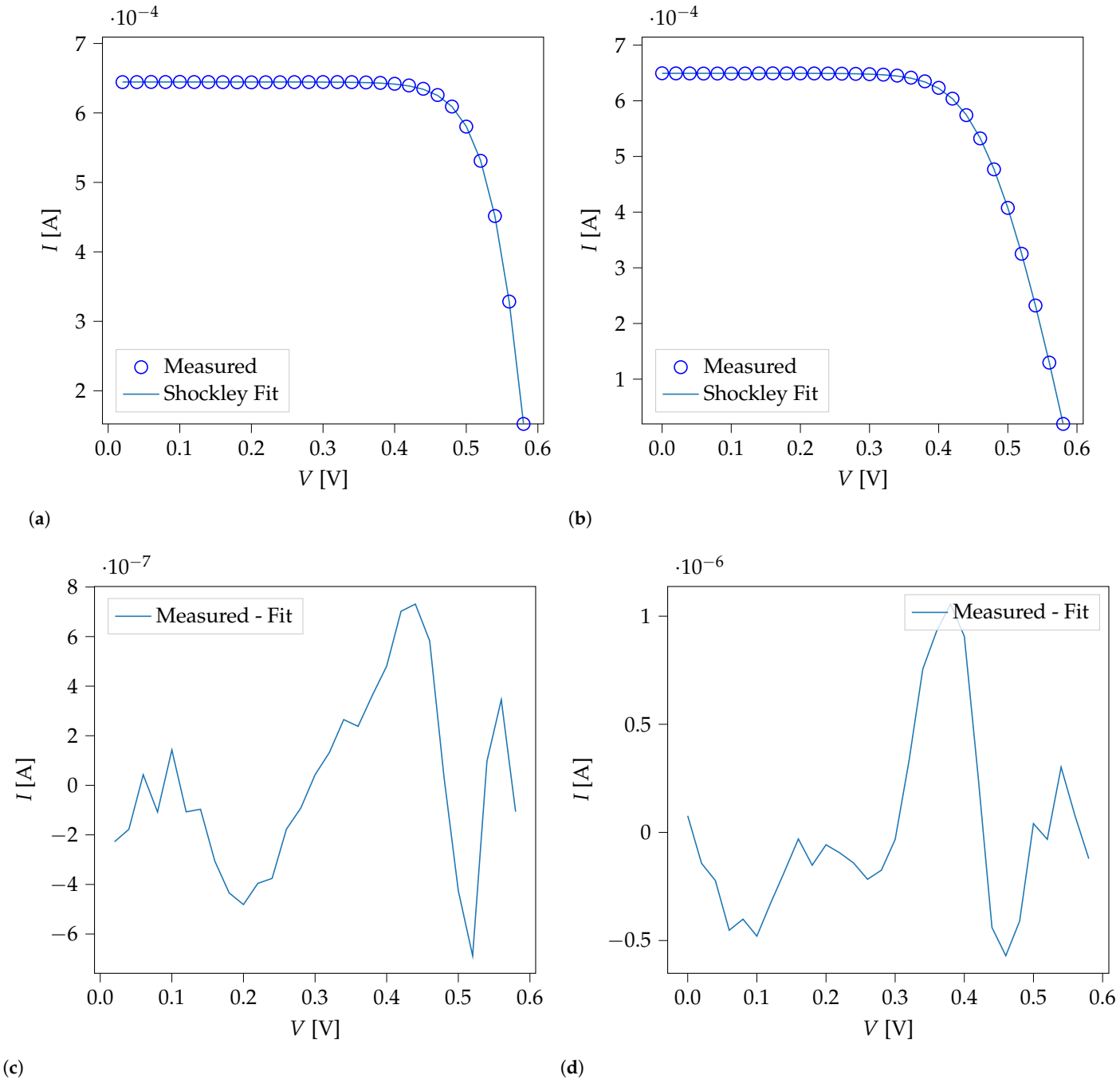


Figure S1. Non-linear least-squares fit and respective point-wise errors for Cell 1 ((a) and (c)), and Cell 2 ((b) and (d))